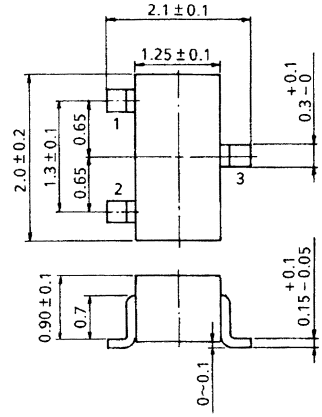
TOSHIBA Field Effect Transistor Silicon P Channel MOS Type

2SJ344

High Speed Switching Applications
Analog Switch Applications

- Low threshold voltage: V_{th} = −0.8~−2.5 V
- High speed
- Enhancement-mode
- Small package
- Complementary to 2SK1827

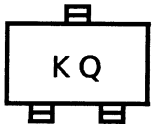
Unit: mm



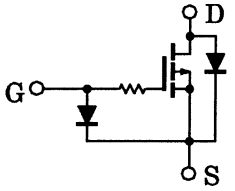
JEDEC	—
JEITA	SC-70
TOSHIBA	2-2E1E

Weight: 0.006 g (typ.)

Marking



Equivalent Circuit



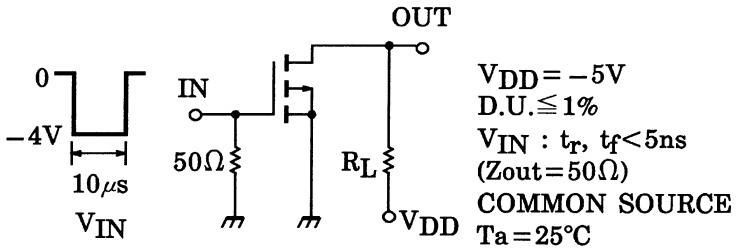
Maximum Ratings (Ta = 25°C)

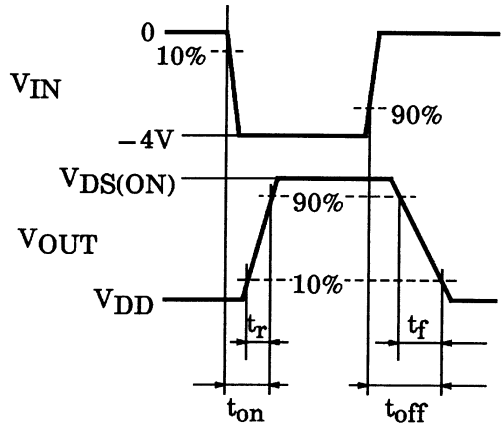
Characteristics	Symbol	Rating	Unit
Drain-source voltage	V_{DS}	−50	V
Gate-source voltage	V_{GSS}	−7	V
DC drain current	I_D	−50	mA
Drain power dissipation	P_D	100	mW
Channel temperature	T_{ch}	150	°C
Storage temperature range	T_{stg}	−55~150	°C

Electrical Characteristics (Ta = 25°C)

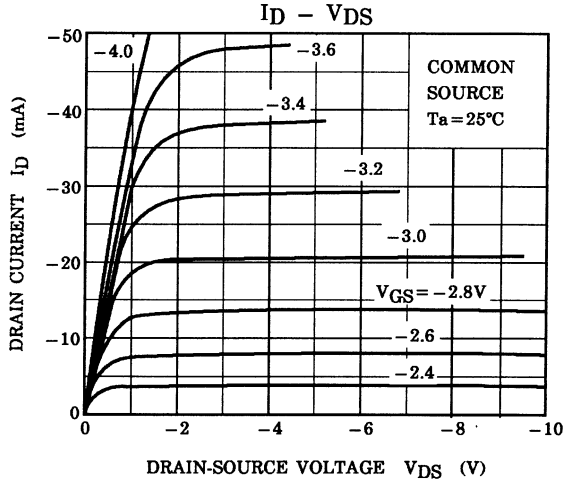
Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gateate leakage current		I_{GSS}	V_{GS} = −7 V, V_{DS} = 0	—	—	−1	μA
Drain-source breakdown voltage		$V_{(BR)\ DSS}$	I_D = −100 μA, V_{GS} = 0	−50	—	—	V
Drain cut-off current		I_{DSS}	V_{DS} = −50 V, V_{GS} = 0	—	—	−1	μA
Gate threshould voltage		V_{th}	V_{DS} = −5 V, I_D = −0.1 mA	−0.8	—	−2.5	V
Forward transfer admittance		$\|Y_{fs}\|$	V_{DS} = −5 V, I_D = −10 mA	15	—	—	mS
Drain-source ON resistance		$R_{DS\ (ON)}$	I_D = −10 mA, V_{GS} = −4 V	—	20	50	Ω
Input capacitance		C_{iss}	V_{DS} = −5 V, V_{GS} = 0, f = 1 MHz	—	10.5	—	pF
Reverse transfer capacitance		C_{rss}	V_{DS} = −5 V, V_{GS} = 0, f = 1 MHz	—	1.9	—	pF
Output capacitance		C_{oss}	V_{DS} = −5 V, V_{GS} = 0, f = 1 MHz	—	7.2	—	pF
Switching time	Turn-on time	t_{on}	V_{DD} = −5 V, I_D = −10 mA, V_{GS} = 0~−4 V	—	0.15	—	μs
	Turn-off time	t_{off}		—	0.13	—	

Switching Time Test Circuit

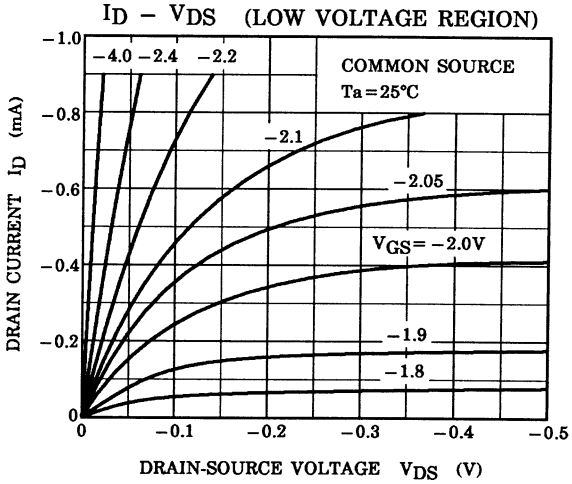




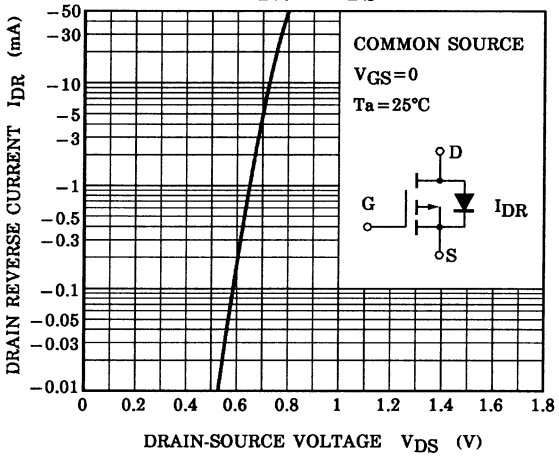
I_D – V_{DS}



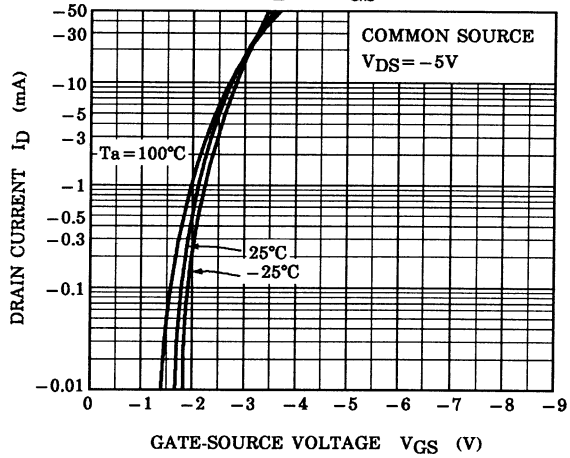
I_D – V_{DS} (LOW VOLTAGE REGION)



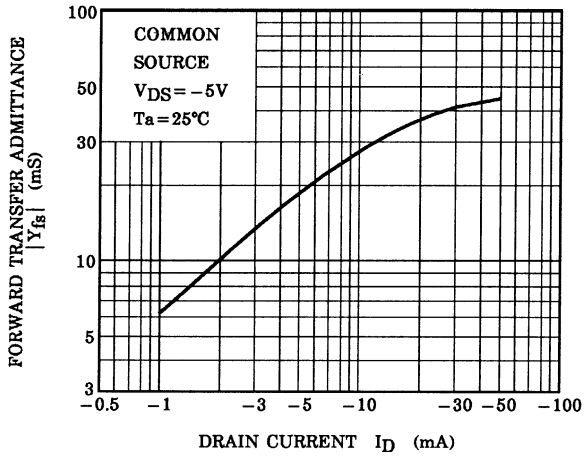
I_{DR} – V_{DS}



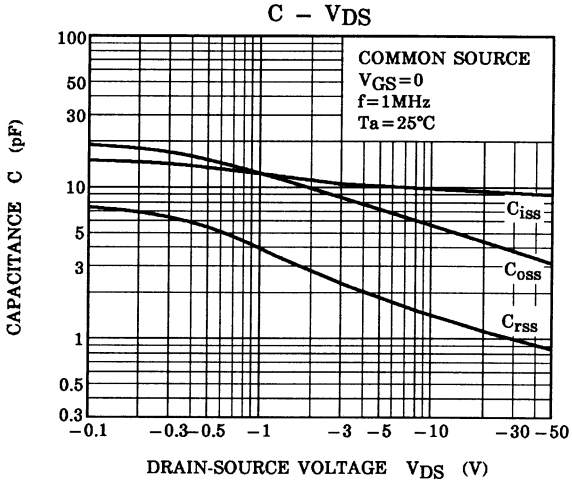
I_D – V_{GS}



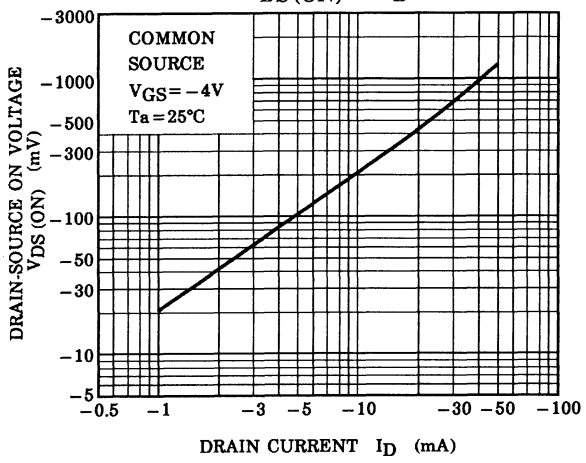
$|Y_{fs}|$ – I_D



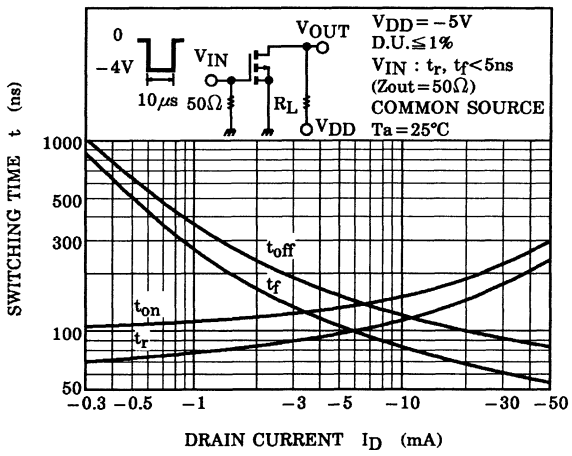
C – V_{DS}



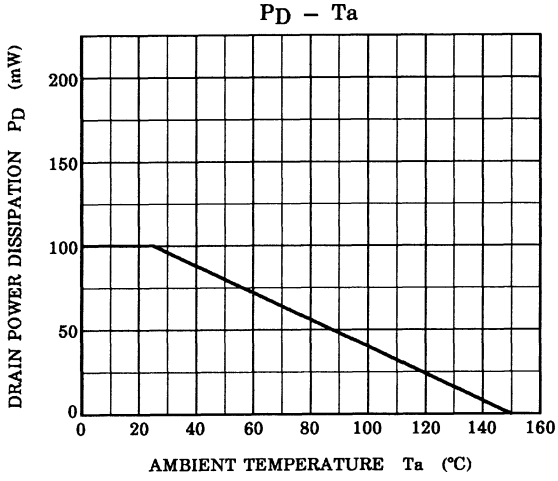
$V_{DS\,(ON)}$ – I_D



t – I_D



P_D – Ta



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